

SEMITOP<sup>®</sup> 3

### 3-phase bridge rectifier + brake chopper +3-phase bridge inverter SK 15 DGDL 126 ET

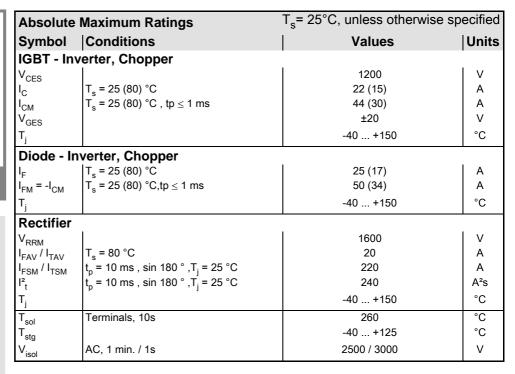
Preliminary Data

#### Features

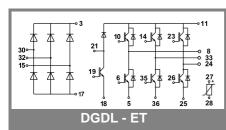
- Compact design
- One screw mounting
- Heat transfer and isolation through direct copper bonded alumium oxide ceramic (DCB)
- Trench technology IGBT
- CAL High Density FWD
- Integrated NTC temperature sensor

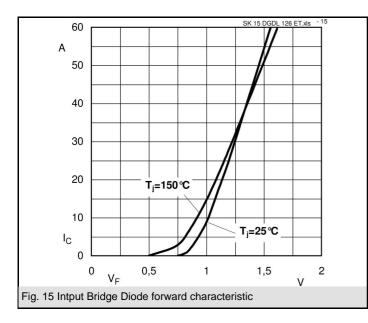
#### **Typical Applications**

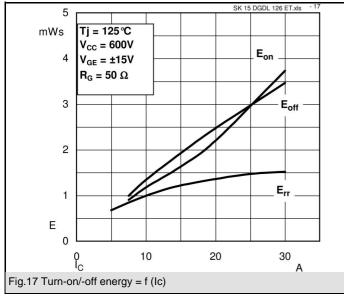
Inverter

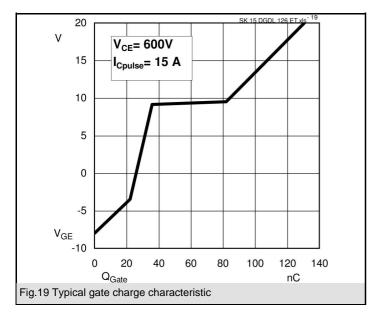


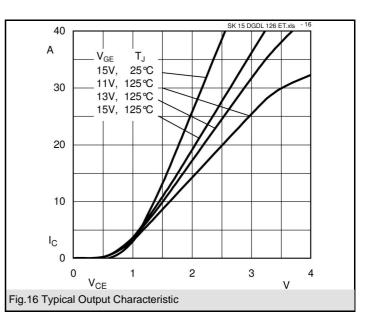
Characteristics		T <sub>s</sub> = 25°C	T <sub>s</sub> = 25°C, unless otherwise specified			
Symbol	Conditions	min.	typ.	max.	Units	
IGBT - Inv	verter, Chopper	·				
V <sub>CEsat</sub>	I <sub>C</sub> = 15 A, T <sub>i</sub> = 25 (125) °C		1,7 (2)	2,1	V	
V <sub>GE(th)</sub>	$V_{GE} = V_{CE}, I_{C} = 0,6 \text{ mA}$	5	5,8	6,5	V	
V <sub>CE(TO)</sub>	T <sub>j</sub> = 25 °C (125) °C		1 (0,9)		V	
r <sub>T</sub>	T <sub>j</sub> = 25 °C (125) °C		45 (70)		mΩ	
Cies	V <sub>CE</sub> = 25 V <sub>GE</sub> = 0 V, f = 1 MHz		1,2		nF	
C <sub>oes</sub>	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		0,1		nF	
C <sub>res</sub>	$V_{CE} = 25 V_{GE} = 0 V, f = 1 MHz$		9,1		nF	
R <sub>th(j-s)</sub>	per IGBT			1,6	K/W	
t <sub>d(on)</sub>	under following conditions		25		ns	
t <sub>r</sub>	$V_{CC}$ = 600 V, $V_{GE}$ = ± 15 V		25		ns	
t <sub>d(off)</sub>	I <sub>C</sub> = 15 A, T <sub>j</sub> = 125 °C		385		ns	
t <sub>f</sub>	$R_{Gon} = R_{Goff} = 30 \ \Omega$		90		ns	
Eon	inductive load		2		mJ	
E <sub>off</sub>			1,8		mJ	
Diode - Ir	verter, Chopper					
V <sub>F</sub> = V <sub>EC</sub>	I <sub>F</sub> = 15 A, T <sub>i</sub> = 25 (125) °C		1,6 (1,6)		V	
V <sub>(TO)</sub>	T <sub>i</sub> = 25 °C (125) °C		1 (0,8)		V	
r <sub>T</sub>	T <sub>j</sub> = 25 °C (125) °C		40 (53)		mΩ	
$R_{th(j-s)}$	per diode			2,1	K/W	
I <sub>RRM</sub>	under following conditions		25		А	
Q <sub>rr</sub>	I <sub>F</sub> = 15 A, V <sub>R</sub> = 600 V		3		μC	
Err	V <sub>GE</sub> = 0 V, T <sub>i</sub> = 125 °C		1,1		mJ	
	di <sub>F/dt</sub> = 900 Å/µs					
Diode rec	tifier				•	
V <sub>F</sub>	I <sub>F</sub> = 15 A, T <sub>i</sub> = 25 °C		1,1		V	
V <sub>(TO)</sub>	T <sub>i</sub> = 150 °C		0,9		V	
r <sub>T</sub>	T <sub>i</sub> = 150 °C		20		mΩ	
$R_{th(j-s)}$	per diode			2	K/W	
	tur sensor	•				
R <sub>ts</sub>	5 %, T <sub>r</sub> = 25 (100 ) °C		5000(493)		Ω	
Mechanic	al data	<u> </u>			•	
w			30		g	
M <sub>s</sub>	Mounting torque			2,5	Nm	

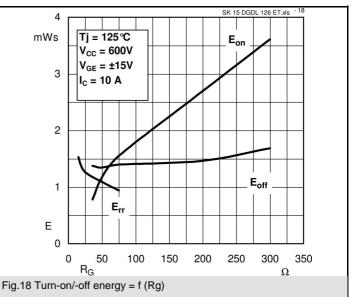


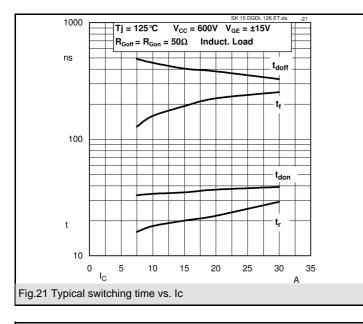


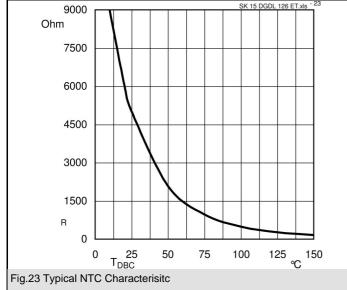


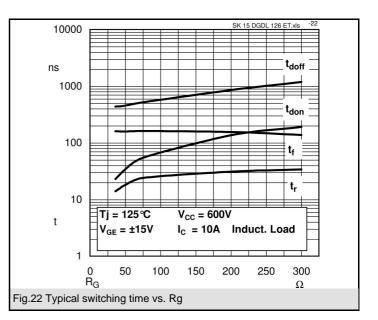


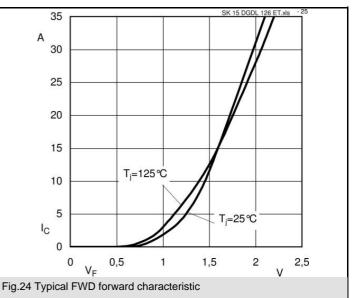


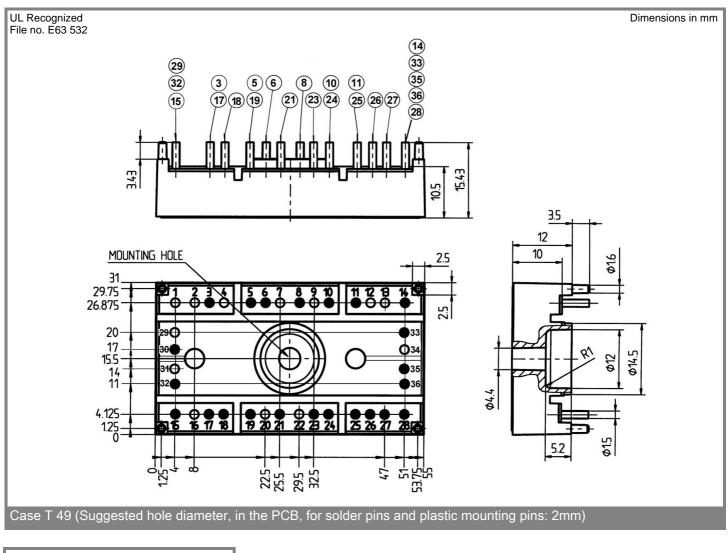


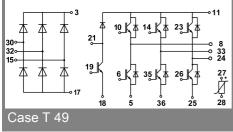












This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX.

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